

General Description

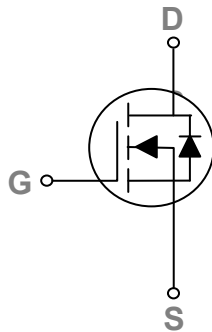
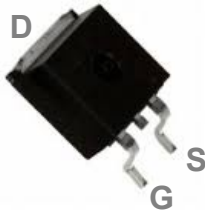
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
30V	2.1mΩ	200A

Features

- 30V, 200A, $R_{DS(ON)} = 2.1m\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

TO263 Pin Configuration



Applications

- MB / VGA / Server Vcore
- POL Applications
- SMPS 2nd SR
- BMS System

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_C=25^\circ\text{C}$) (Chip Limitation)	200	A
	Drain Current – Continuous ($T_C=100^\circ\text{C}$) (Chip Limitation)	126	A
I_{DM}	Drain Current – Pulsed ¹	800	A
EAS	Single Pulse Avalanche Energy ²	245	mJ
IAS	Single Pulse Avalanche Current ²	70	A
P_D	Power Dissipation ($T_C=25^\circ\text{C}$)	139	W
	Power Dissipation – Derate above 25°C	1.1	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.68	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)
Static State Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=27V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=85^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(ON)}$	Static Drain-Source On-Resistance ³	$V_{GS}=10V, I_D=30A$	---	1.7	2.1	$m\Omega$
		$V_{GS}=4.5V, I_D=15A$	---	2.0	2.6	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1	1.6	2.5	V
gfs	Forward Transconductance	$V_{DS}=10V, I_D=15A$	---	30	---	S

Dynamic Characteristics

Q_g	Total Gate Charge ^{3,4}	$V_{DS}=15V, V_{GS}=4.5V, I_D=10A$	---	65	120	nC
Q_{gs}	Gate-Source Charge ^{3,4}		---	16	30	
Q_{gd}	Gate-Drain Charge ^{3,4}		---	21	40	
$T_{d(on)}$	Turn-On Delay Time ^{3,4}	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega$ $I_D=1A$	---	28	56	ns
T_r	Rise Time ^{3,4}		---	45	90	
$T_{d(off)}$	Turn-Off Delay Time ^{3,4}		---	105	200	
T_f	Fall Time ^{3,4}		---	40	80	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, F=1\text{MHz}$	---	7720	11000	pF
C_{oss}	Output Capacitance		---	945	1400	
C_{rss}	Reverse Transfer Capacitance		---	435	650	
R_g	Gate resistance		$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	1.2	

Guaranteed Avalanche Energy

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy	$V_{DD}=25V, L=0.1\text{mH}, I_{AS}=30A$	45	---	---	mJ

Drain-Source Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	200	A
I_{SM}	Pulsed Source Current ³		---	---	400	A
V_{SD}	Diode Forward Voltage ³	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=70A, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$.
3. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

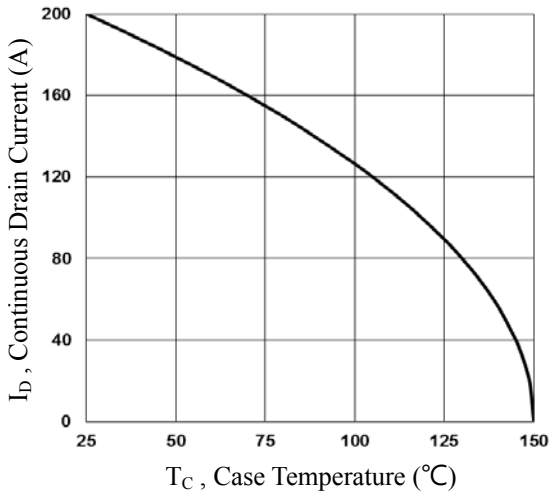


Fig.1 Continuous Drain Current vs. T_c

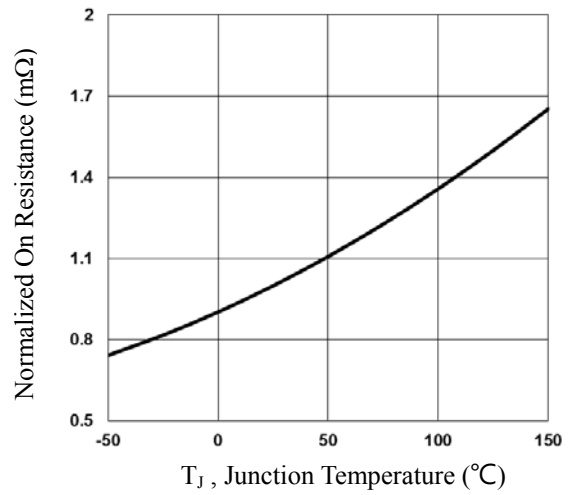


Fig.2 Normalized R_{DSon} vs. T_j

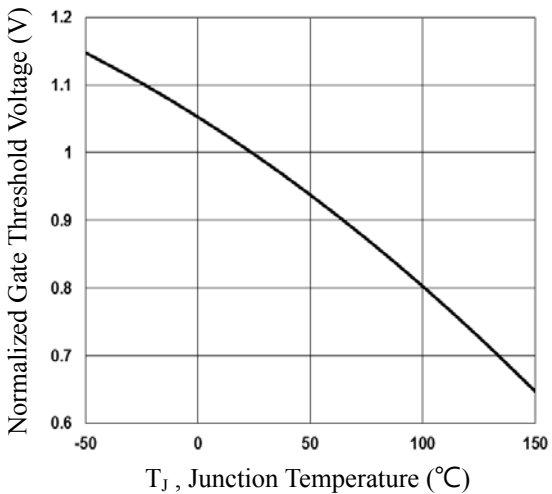


Fig.3 Normalized V_{th} vs. T_j

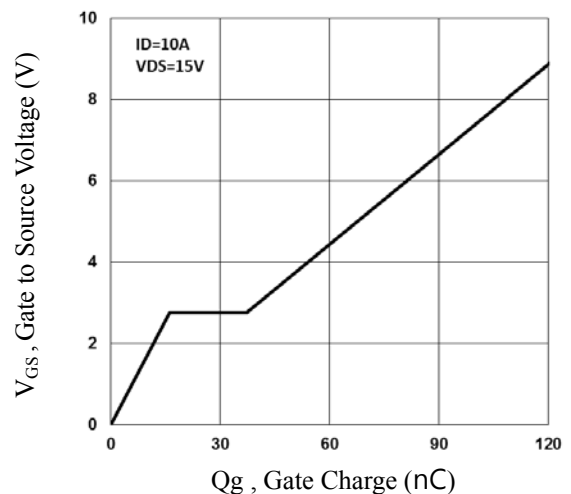


Fig.4 Gate Charge Waveform

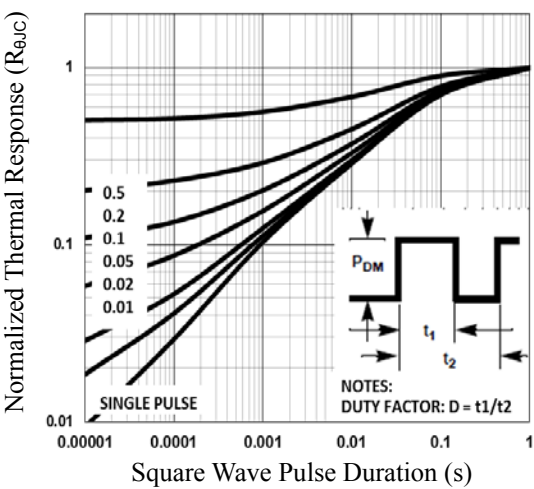


Fig.5 Normalized Transient Impedance

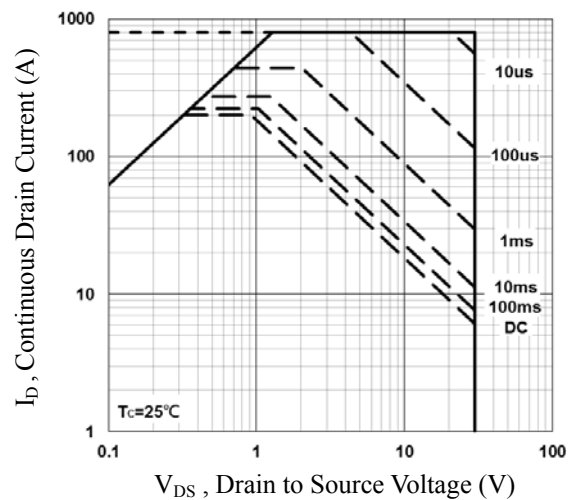


Fig.6 Maximum Safe Operation Area

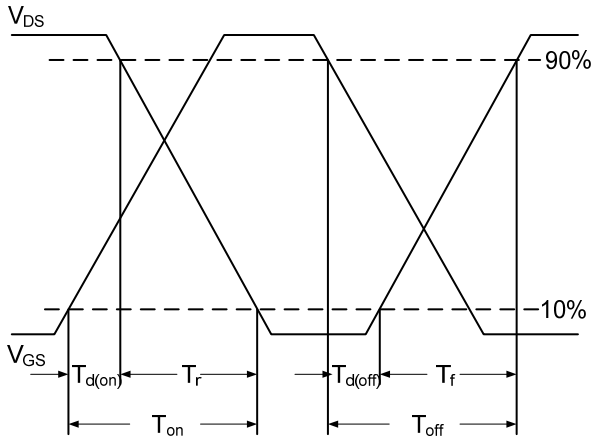


Fig.7 Switching Time Waveform

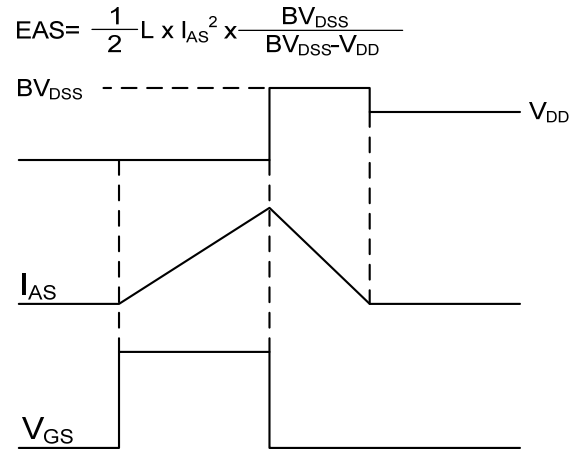


Fig.8 EAS Waveform